

PMD4003K

MOSFET driver

Rev. 01 — 3 November 2006

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor and high-speed switching diode to protect the base-emitter junction in reverse direction in a SOT346 (SC-59A/TO-236) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low V_{CEsat} (BISS) transistor and high-speed switching diode as driver
- High-speed switching diode to protect the base-emitter junction
- Application-optimized pinout
- Internal connections to minimize layout effort
- Space-saving solution
- Reduces component count

1.3 Applications

- Power MOSFET driver

1.4 Quick reference data

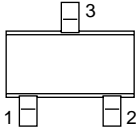
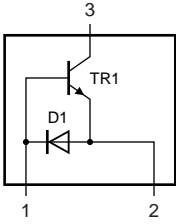
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
NPN transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I_C	collector current		-	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	2	A
Diode						
I_F	forward current		-	-	-0.2	A
V_F	forward voltage	$I_F = -200$ mA	[1]	-	-1.1	V

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	base TR1, cathode D1		
2	emitter TR1, anode D1		
3	collector TR1		

006aaa655

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMD4003K	SC-59A	plastic surface-mounted package; 3 leads	SOT346

4. Marking

Table 4. Marking codes

Type number	Marking code
PMD4003K	D3

5. Limiting values

Table 5. Limiting values

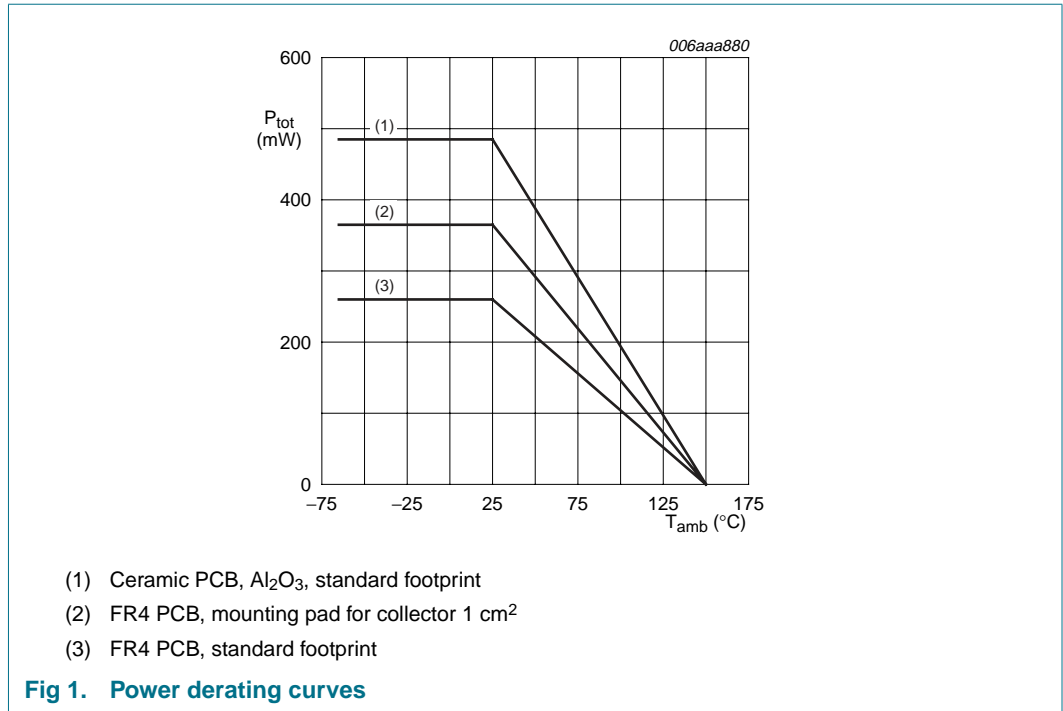
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
NPN transistor						
V_{CBO}	collector-base voltage	open emitter	-	40	V	
V_{CEO}	collector-emitter voltage	open base	-	40	V	
I_C	collector current		-	1	A	
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	2	A	
I_B	base current		-	0.3	A	
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	1	A	
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	260	mW
			[2]	-	365	mW
			[3]	-	485	mW
Diode						
I_F	forward current		-	-0.2	A	
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ ms; $\delta = 0.25$	-	-0.6	A	
I_{FSM}	non-repetitive peak forward current	square wave				
		$t_p \leq 1$ μ s	-	-9	A	
		$t_p \leq 100$ μ s	-	-3	A	
		$t_p \leq 10$ ms	-	-1.7	A	
Device						
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-65	+150	°C	
T_{stg}	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

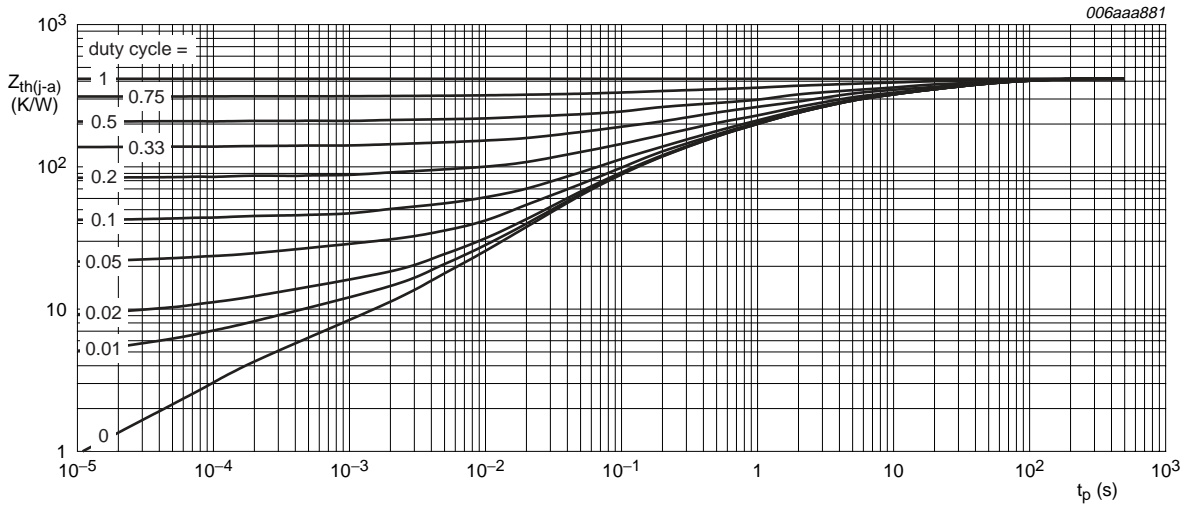


6. Thermal characteristics

Table 6. Thermal characteristics

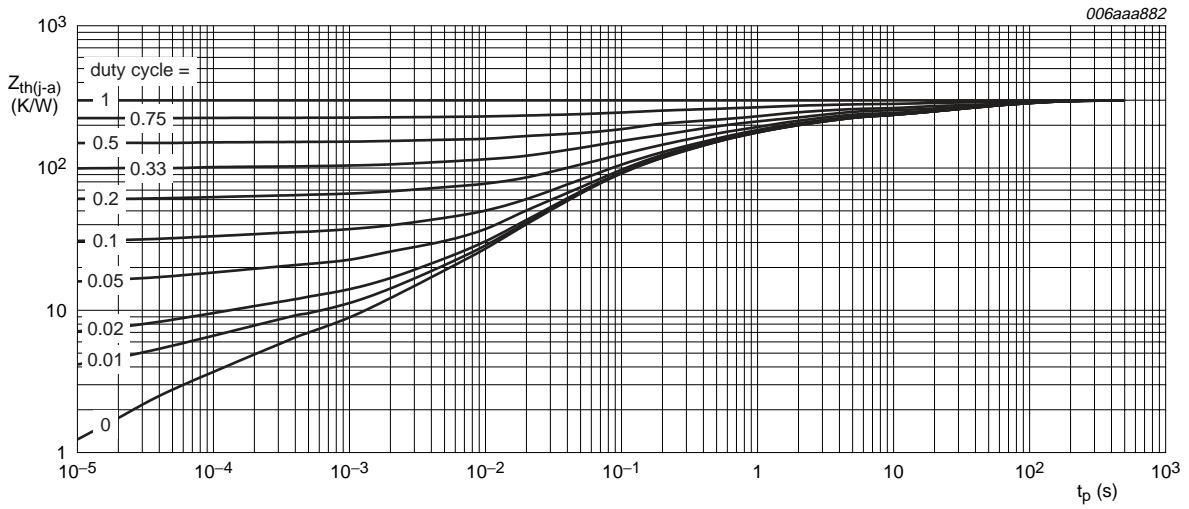
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
NPN transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	480	K/W
			[2]	-	340	K/W
			[3]	-	255	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



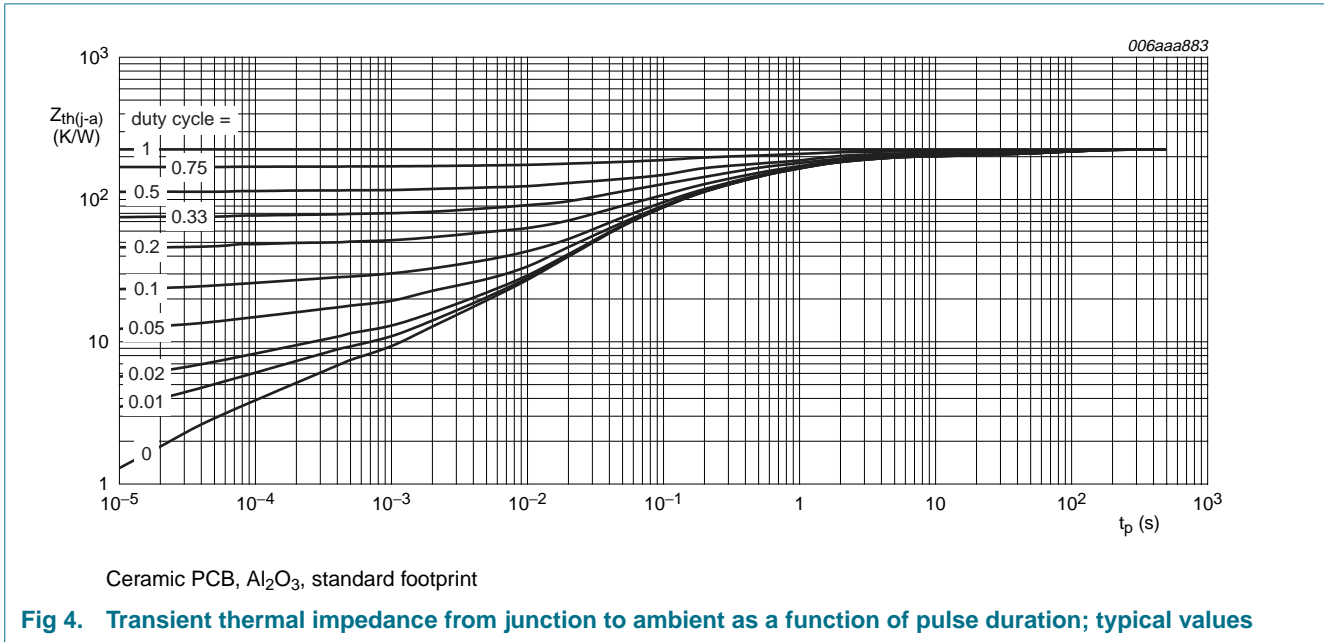
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

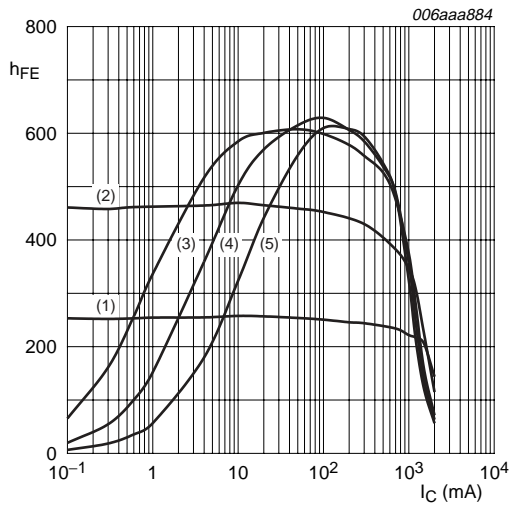


7. Characteristics

Table 7. Characteristics

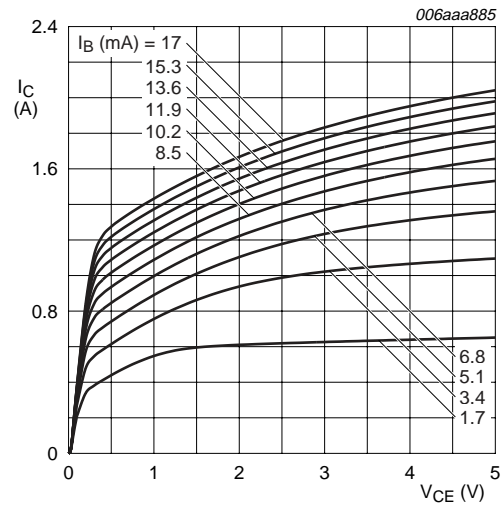
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
NPN transistor							
I_{CBO}	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0\text{ A}$	-	-	100	nA	
		$V_{CB} = 40\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	-	-	50	μA	
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	300	450	-		
		$V_{CE} = 5\text{ V}; I_C = 200\text{ mA}$	300	450	830		
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	[1]	300	400	-	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	[1]	200	340	-	
		$V_{CE} = 5\text{ V}; I_C = 2\text{ A}$	[1]	75	120	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	30	80	mV	
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	[1]	-	100	120	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1]	-	180	230	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}$	[1]	-	360	440	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	0.75	0.9	V	
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	[1]	-	0.9	1.1	V
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1]	-	1	2	V
		$I_C = 2\text{ A}; I_B = 200\text{ mA}$	[1]	-	1.1	1.3	V
V_{BE}	base-emitter voltage	$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	[1]	-	760	-	mV
Diode							
V_F	forward voltage	$I_F = -200\text{ mA}$	[1]	-	-	-1.1	V
Device							
t_d	delay time	$I_C = 0.5\text{ A}; I_B = 25\text{ mA}$	-	5	-	ns	
t_r	rise time		-	27	-	ns	
t_{on}	turn-on time		-	32	-	ns	
t_s	storage time		-	1520	-	ns	
t_f	fall time		-	184	-	ns	
t_{off}	turn-off time		-	1704	-	ns	
Device with optional capacitor C1							
t_d	delay time	$I_C = 0.5\text{ A}; I_B = 25\text{ mA}; C1 = 2.2\text{ nF}$	-	2	-	ns	
t_r	rise time		-	2	-	ns	
t_{on}	turn-on time		-	4	-	ns	
t_s	storage time		-	150	-	ns	
t_f	fall time		-	154	-	ns	
t_{off}	turn-off time		-	304	-	ns	

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



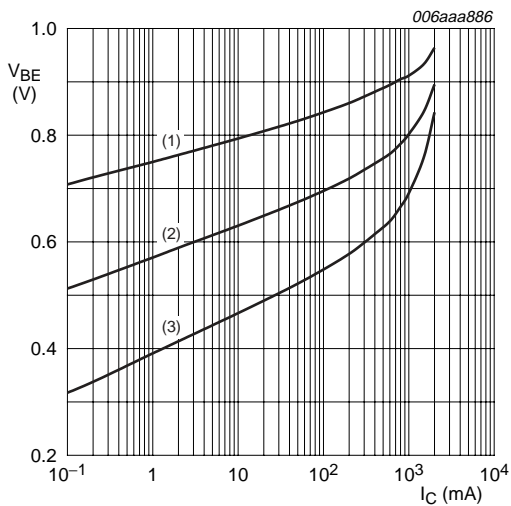
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55^\circ C$
 (2) $T_{amb} = 25^\circ C$
 (3) $T_{amb} = 100^\circ C$
 (4) $T_{amb} = 125^\circ C$
 (5) $T_{amb} = 150^\circ C$

Fig 5. DC current gain as a function of collector current; typical values



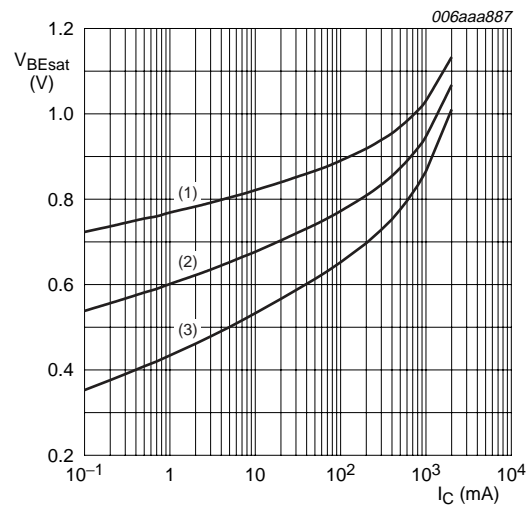
$T_{amb} = 25^\circ C$

Fig 6. Collector current as a function of collector-emitter voltage; typical values



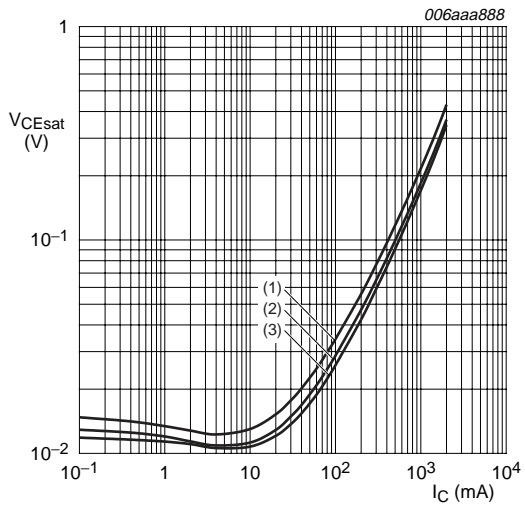
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55^\circ C$
 (2) $T_{amb} = 25^\circ C$
 (3) $T_{amb} = 100^\circ C$

Fig 7. Base-emitter voltage as a function of collector current; typical values



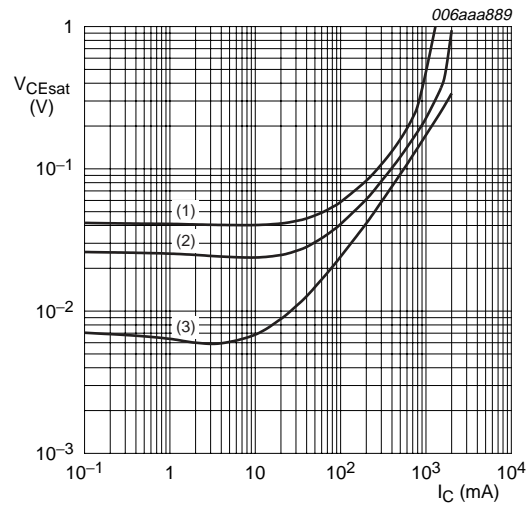
$I_C/I_B = 20$
 (1) $T_{amb} = -55^\circ C$
 (2) $T_{amb} = 25^\circ C$
 (3) $T_{amb} = 100^\circ C$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 - (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 - (3) $T_{amb} = -55\text{ }^\circ\text{C}$

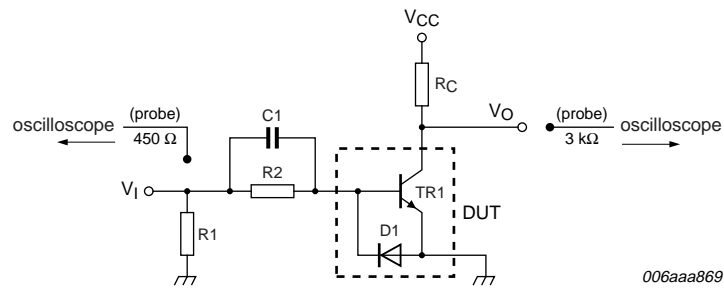
Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



- $T_{amb} = 25\text{ }^\circ\text{C}$
- (1) $I_C/I_B = 100$
 - (2) $I_C/I_B = 50$
 - (3) $I_C/I_B = 10$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

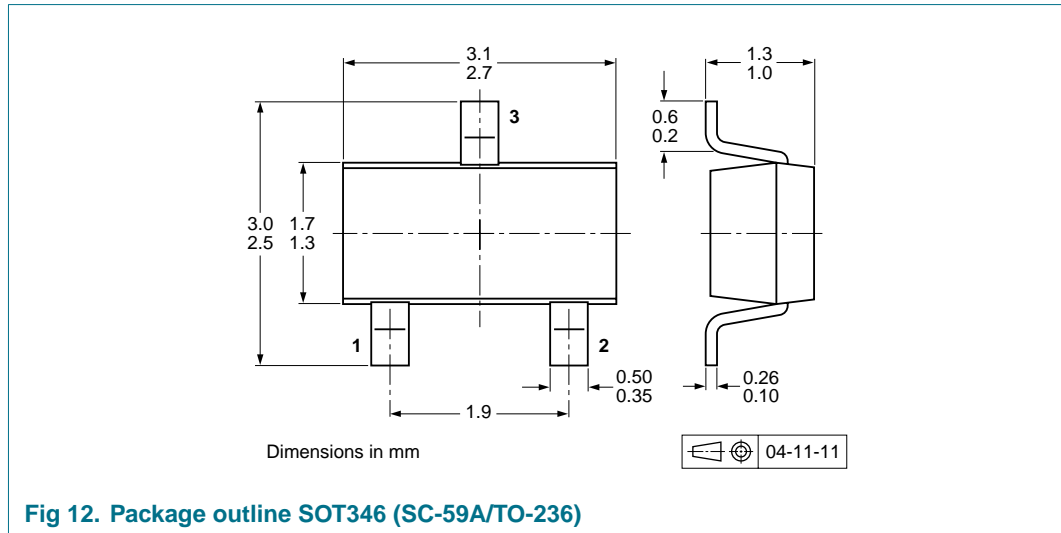
8. Test information



$I_C = 0.5\text{ A}; I_B = 25\text{ mA}; R_1 = 68\text{ }\Omega; R_2 = 300\text{ }\Omega; R_C = 18\text{ }\Omega; C_1 = 2.2\text{ nF}$

Fig 11. Test circuit for switching times

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMD4003K	SOT346	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 15](#).

11. Soldering

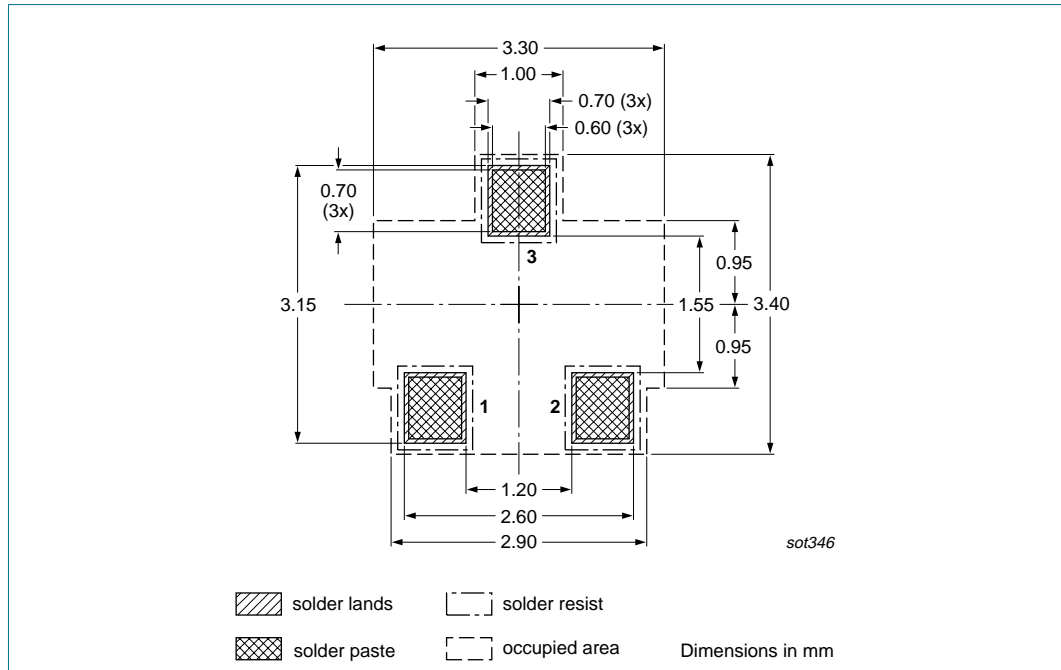


Fig 13. Reflow soldering footprint

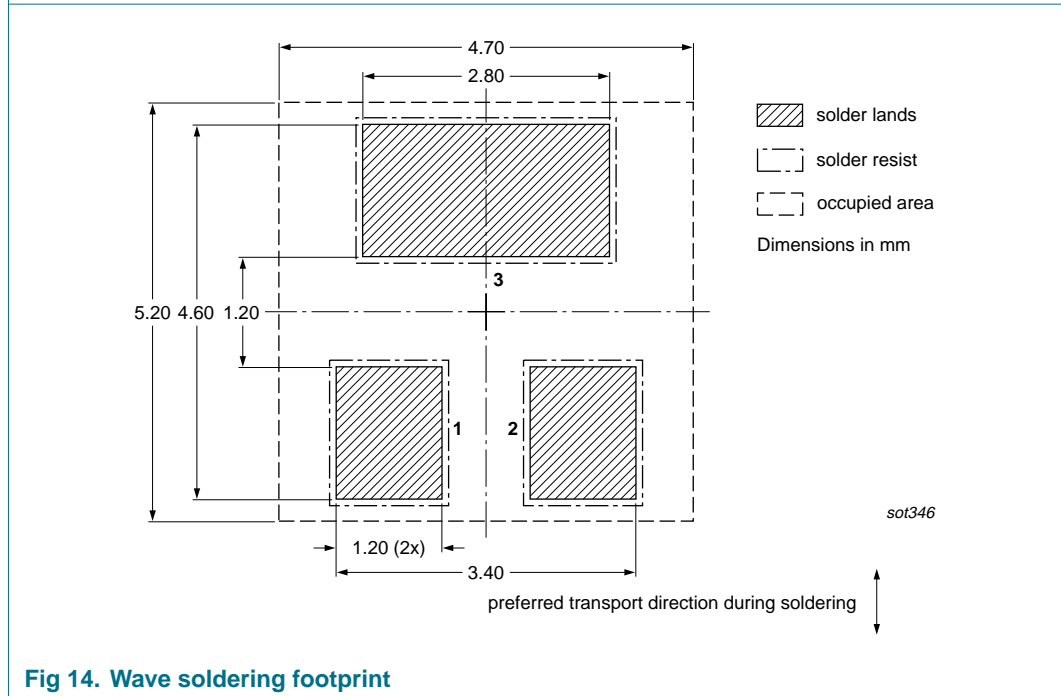
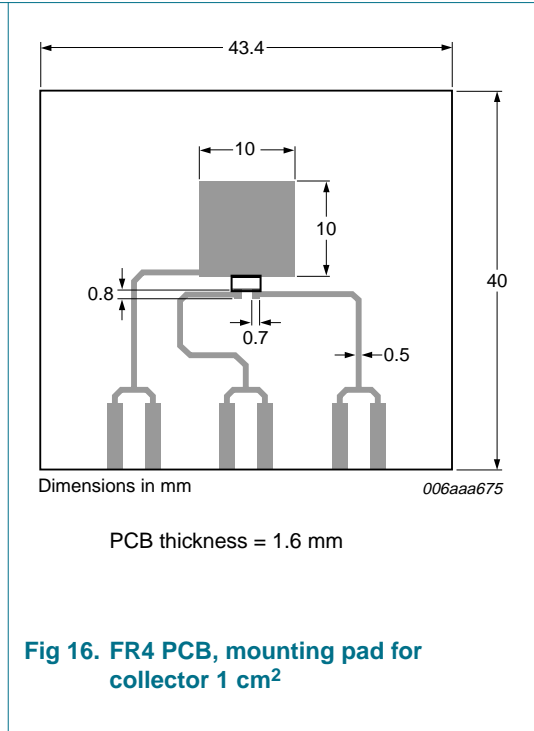
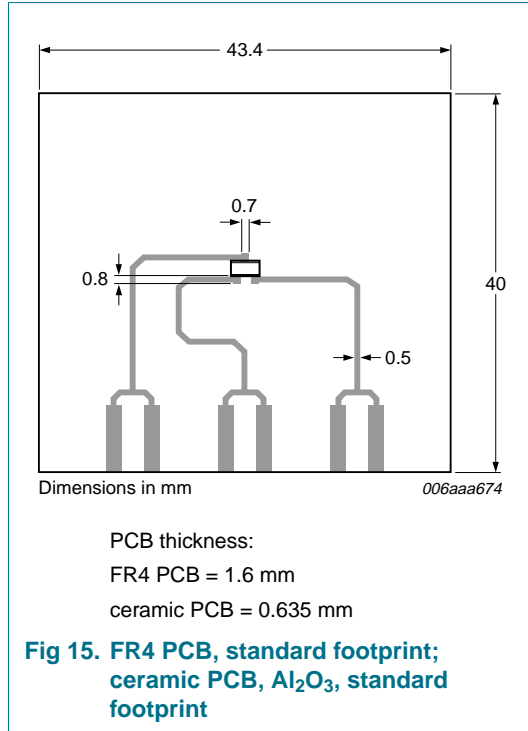


Fig 14. Wave soldering footprint

12. Mounting



13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMD4003K_1	20061103	Product data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 3 November 2006

Document identifier: PMD4003K_1